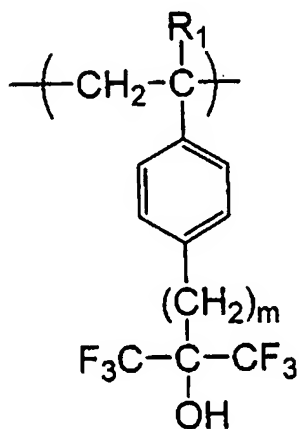


## THE CLAIMS

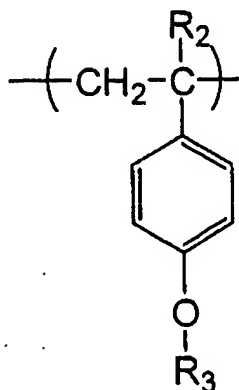
*A listing of the claims presented in this patent application appears below. This listing replaces all prior versions and listing of claims in this patent application.*

**Claim 1 (withdrawn):** A pattern formation material comprising:  
a polymer including a first unit represented by Chemical Formula 1 and a second unit represented by Chemical Formula 2; and  
an acid generator:

Chemical Formula 1:



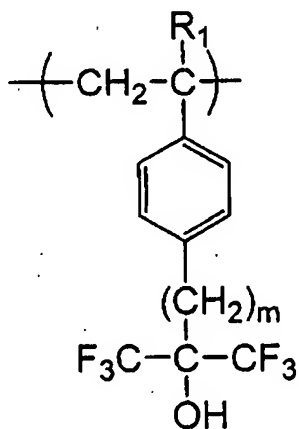
Chemical Formula 2:



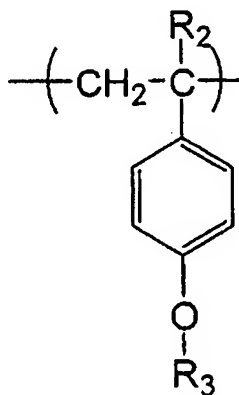
wherein  $\text{R}_1$  and  $\text{R}_2$  are the same or different and selected from the group consisting of an alkyl group, a chlorine atom and an alkyl group including a fluorine atom;  $\text{R}_3$  is a protecting group released by an acid; and  $m$  is an integer of 0 through 5.

**Claim 2 (withdrawn):** A pattern formation material comprising:  
a polymer including a first unit represented by Chemical Formula 3, a second unit represented by Chemical Formula 4 and a third unit represented by Chemical Formula 5; and  
an acid generator:

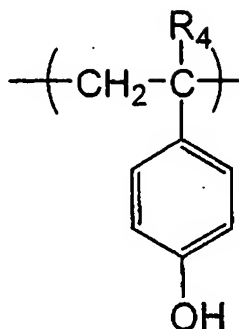
Chemical Formula 3:



Chemical Formula 4:



Chemical Formula 5:

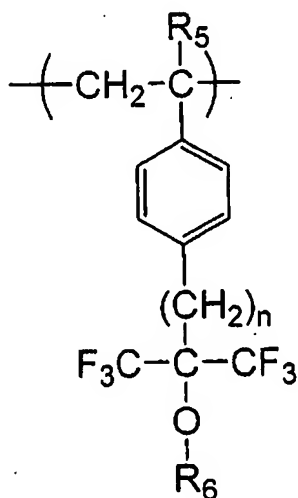


wherein  $\text{R}_1$ ,  $\text{R}_2$  and  $\text{R}_4$  are the same or different and selected from the group consisting of an alkyl group, a chlorine atom and an alkyl group including a fluorine atom;  $\text{R}_3$  is a protecting group released by an acid; and  $m$  is an integer of 0 through 5.

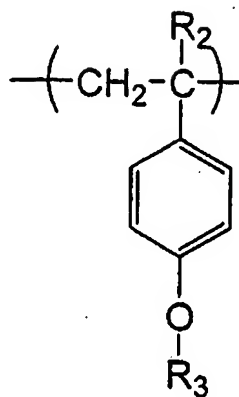
**Claim 3 (withdrawn):** A pattern formation material comprising:

a polymer including a first unit represented by Chemical Formula 6 and a second unit represented by Chemical Formula 7; and  
an acid generator:

Chemical Formula 6:



Chemical Formula 7:



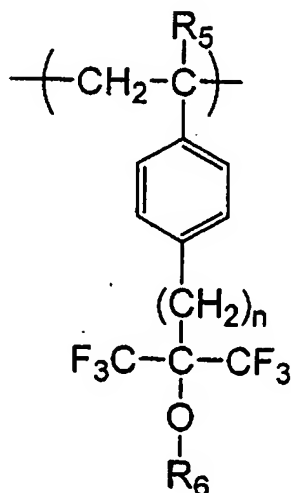
wherein R<sub>2</sub> and R<sub>5</sub> are the same or different and selected from the group consisting of an alkyl group, a chlorine atom and an alkyl group including a fluorine atom; R<sub>3</sub> and R<sub>6</sub> are the same or different, at least one of which is a protecting group released by an acid; and n is an integer of 0 through 5.

**Claim 4 (withdrawn):** A pattern formation material comprising:

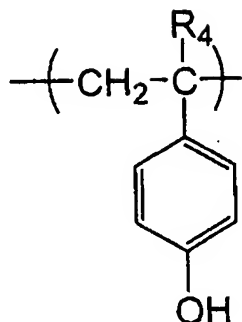
a polymer including a first unit represented by Chemical Formula 8 and a second unit represented by Chemical Formula 9; and

an acid generator:

Chemical Formula 8:



Chemical Formula 9:

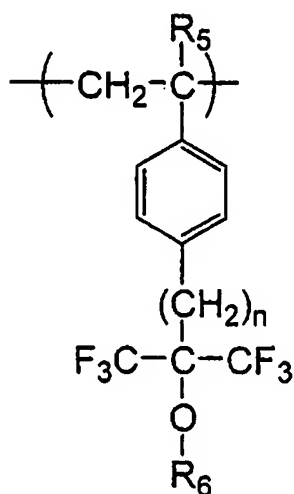


wherein R<sub>4</sub> and R<sub>5</sub> are the same or different and selected from the group consisting of an alkyl group, a chlorine atom and an alkyl group including a fluorine atom; R<sub>6</sub> is a protecting group released by an acid; and n is an integer of 0 through 5.

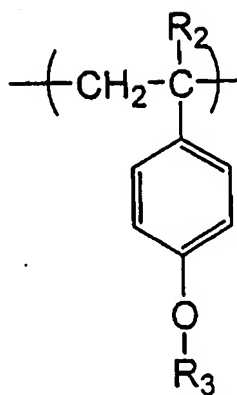
**Claim 5 (withdrawn):** A pattern formation material comprising:

a polymer including a first unit represented by Chemical Formula 10, a second unit represented by Chemical Formula 11 and a third unit represented by Chemical Formula 12; and  
an acid generator:

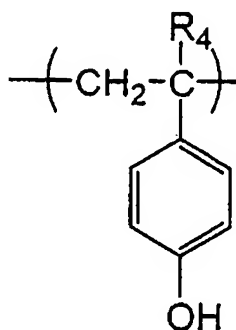
Chemical Formula 10:



Chemical Formula 11:



Chemical Formula 12:

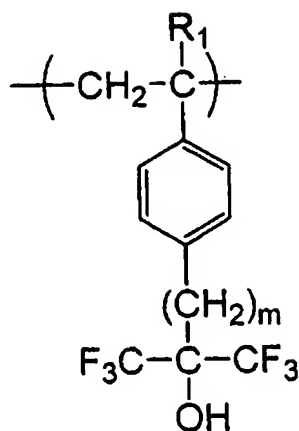


wherein  $\text{R}_2$ ,  $\text{R}_4$  and  $\text{R}_5$  are the same or different and selected from the group consisting of an alkyl group, a chlorine atom and an alkyl group including a fluorine atom;  $\text{R}_3$  and  $\text{R}_6$  are the same or different, at least one of which is a protecting group released by an acid; and  $n$  is an integer of 0 through 5.

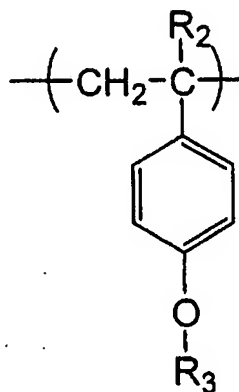
**Claim 6 (original):** A pattern formation method comprising the steps of:

forming a resist film by applying, on a substrate, a pattern formation material containing a polymer including a first unit represented by Chemical Formula 1 and a second unit represented by Chemical Formula 2, and an acid generator:

Chemical Formula 1:



Chemical Formula 2:



wherein  $\text{R}_1$  and  $\text{R}_2$  are the same or different and selected from the group consisting of an alkyl group, a chlorine atom and an alkyl group including a fluorine atom;  $\text{R}_3$  is a protecting group released by an acid; and  $m$  is an integer of 0 through 5;

irradiating said resist film with exposing light of a wavelength shorter than a 180 nm band for pattern exposure; and

forming a resist pattern by developing said resist film after the pattern exposure.

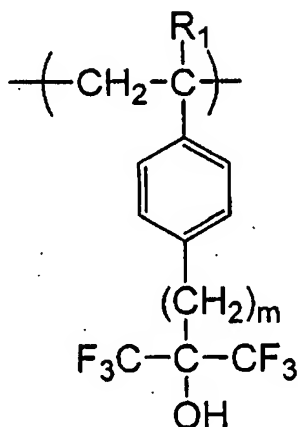
**Claim 7 (original):** The pattern formation method of Claim 6, wherein said exposing light is a Xe<sub>2</sub> laser beam, a F<sub>2</sub> laser beam, a Kr<sub>2</sub> laser beam, an ArKr laser beam or an Ar<sub>2</sub> laser beam.

**Claim 8 (original):** The pattern formation method of Claim 6, wherein said exposing light is soft-X rays.

**Claim 9 (original):** The pattern formation method of Claim 6, wherein said exposing light is hard-X rays.

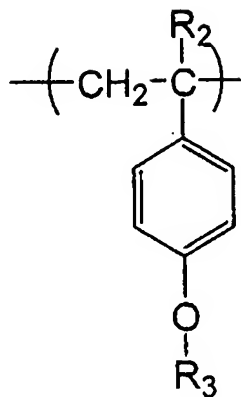
**Claim 10 (original):** A pattern formation method comprising the steps of:  
forming a resist film by applying, on a substrate, a pattern formation material containing a polymer including a first unit represented by Chemical Formula 3, a second unit represented by Chemical Formula 4 and a third unit represented by Chemical Formula 5, and an acid generator:

Chemical Formula 3:

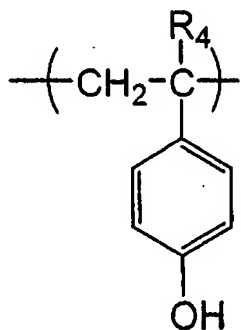




Chemical Formula 4:



Chemical Formula 5:



wherein  $\text{R}_1$ ,  $\text{R}_2$  and  $\text{R}_4$  are the same or different and selected from the group consisting of an alkyl group, a chlorine atom and an alkyl group including a fluorine atom;  $\text{R}_3$  is a protecting group released by an acid; and  $m$  is an integer of 0 through 5;

irradiating said resist film with exposing light of a wavelength shorter than a 180 nm band for pattern exposure; and

forming a resist pattern by developing said resist film after the pattern exposure.

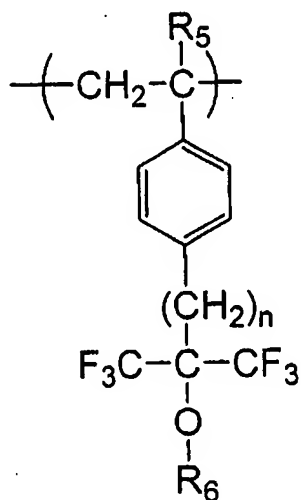
**Claim 11 (original):** The pattern formation method of Claim 10, wherein said exposing light is a  $\text{Xe}_2$  laser beam, a  $\text{F}_2$  laser beam, a  $\text{Kr}_2$  laser beam, an ArKr laser beam or an  $\text{Ar}_2$  laser beam.

**Claim 12 (original):** The pattern formation method of Claim 10, wherein said exposing light is soft-X rays.

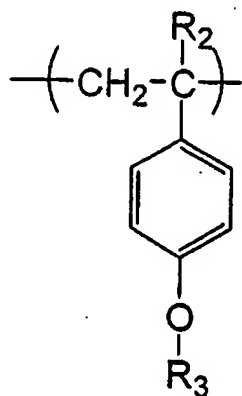
**Claim 13 (original):** The pattern formation method of Claim 10, wherein said exposing light is hard-X rays.

**Claim 14 (original):** A pattern formation method comprising the steps of:  
forming a resist film by applying, on a substrate, a pattern formation material containing a polymer including a first unit represented by Chemical Formula 6 and a second unit represented by Chemical Formula 7, and an acid generator:

Chemical Formula 6:



Chemical Formula 7:



wherein R<sub>2</sub> and R<sub>5</sub> are the same or different and selected from the group consisting of an alkyl group, a chlorine atom and an alkyl group including a fluorine atom; R<sub>3</sub> and R<sub>6</sub> are the

same or different, at least one of which is a protecting group released by an acid; and n is an integer of 0 through 5;

irradiating said resist film with exposing light of a wavelength shorter than a 180 nm band for pattern exposure; and

forming a resist pattern by developing said resist film after the pattern exposure.

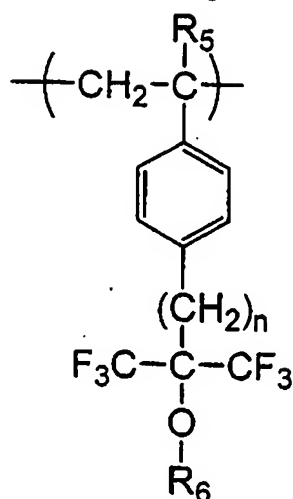
**Claim 15 (original):** The pattern formation method of Claim 14, wherein said exposing light is a Xe<sub>2</sub> laser beam, a F<sub>2</sub> laser beam, a Kr<sub>2</sub> laser beam, an ArKr laser beam or an Ar<sub>2</sub> laser beam.

**Claim 16 (original):** The pattern formation method of Claim 14, wherein said exposing light is soft-X rays.

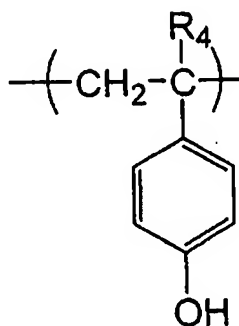
**Claim 17 (original):** The pattern formation method of Claim 14, wherein said exposing light is hard-X rays.

**Claim 18 (original):** A pattern formation method comprising the steps of:  
forming a resist film by applying, on a substrate, a pattern formation material containing a polymer including a first unit represented by Chemical Formula 8 and a second unit represented by Chemical Formula 9, and an acid generator:

Chemical Formula 8:



Chemical Formula 9:



wherein  $\text{R}_4$  and  $\text{R}_5$  are the same or different and selected from the group consisting of an alkyl group, a chlorine atom and an alkyl group including a fluorine atom;  $\text{R}_6$  is a protecting group released by an acid; and  $n$  is an integer of 0 through 5;

irradiating said resist film with exposing light of a wavelength shorter than a 180 nm band for pattern exposure; and

forming a resist pattern by developing said resist film after the pattern exposure.

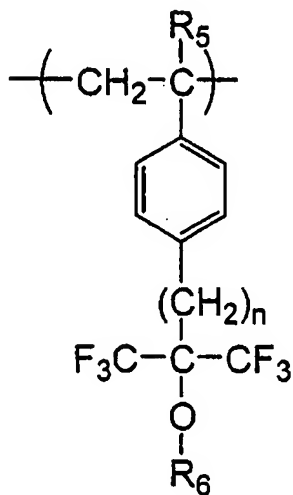
**Claim 19 (original):** The pattern formation method of Claim 18, wherein said exposing light is a Xe<sub>2</sub> laser beam, a F<sub>2</sub> laser beam, a Kr<sub>2</sub> laser beam, an ArKr laser beam or an Ar<sub>2</sub> laser beam.

**Claim 20 (original):** The pattern formation method of Claim 18, wherein said exposing light is soft-X rays.

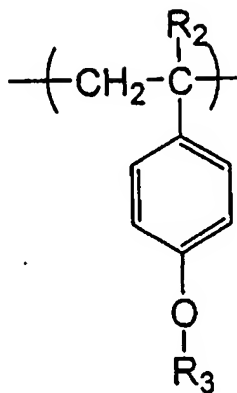
**Claim 21 (original):** The pattern formation method of Claim 18, wherein said exposing light is hard-X rays.

**Claim 22 (original):** A pattern formation method comprising the steps of:  
forming a resist film by applying, on a substrate, a pattern formation material containing a polymer including a first unit represented by Chemical Formula 10, a second unit represented by Chemical Formula 11 and a third unit represented by Chemical Formula 12, and an acid generator:

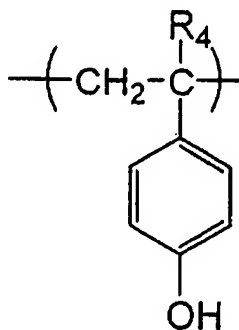
Chemical Formula 10:



Chemical Formula 11:



Chemical Formula 12:



wherein  $\text{R}_2$ ,  $\text{R}_4$  and  $\text{R}_5$  are the same or different and selected from the group consisting of an alkyl group, a chlorine atom and an alkyl group including a fluorine atom;  $\text{R}_3$  and  $\text{R}_6$  are the same or different, at least one of which is a protecting group released by an acid; and  $n$  is an integer of 0 through 5;

irradiating said resist film with exposing light of a wavelength shorter than a 180 nm band for pattern exposure; and

forming a resist pattern by developing said resist film after the pattern exposure.

**Claim 23 (original):** The pattern formation method of Claim 22, wherein said exposing light is a  $\text{Xe}_2$  laser beam, a  $\text{F}_2$  laser beam, a  $\text{Kr}_2$  laser beam, an ArKr laser beam or an  $\text{Ar}_2$  laser beam.

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**Claim 24 (original):** The pattern formation method of Claim 22, wherein said exposing light is soft-X rays.

**Claim 25 (original):** The pattern formation method of Claim 22, wherein said exposing light is hard-X rays.